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(54) Title: A SEMICONDUCTOR ARRANGEMENT AND A METHOD FOR MANUFACTURING THE SAME

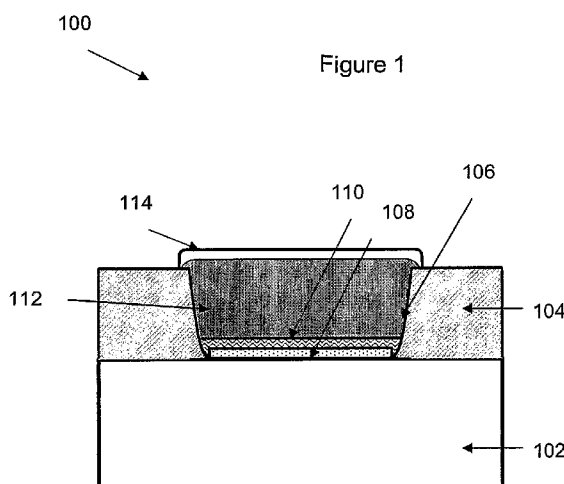


Figure 1

(57) Abstract: A method for manufacturing a semiconductor arrangement is disclosed. The method comprises forming at least one trench in a dielectric layer, thereby exposing a portion of a semiconductor substrate, forming a silicon-germanium buffer layer at least on the bottom of the at least one trench, forming a germanium seed layer on the silicon-germanium buffer layer and forming a germanium layer on the germanium seed layer. A semiconductor arrangement is also disclosed. The semiconductor arrangement comprises a semiconductor substrate, a dielectric layer disposed above the semiconductor substrate, at least one trench in the dielectric layer exposing a portion of the semiconductor substrate, a silicon-germanium buffer layer disposed above at least the bottom of the at least one trench, a germanium seed layer disposed above the silicon-germanium buffer layer and a germanium layer disposed above the germanium seed layer.

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